



N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD16412Q5A

FEATURES

- Ultra Low Qg and Qgd
- **Low Thermal Resistance**
- **Avalanche Rated**
- Pb Free Terminal Plating
- **RoHS Compliant**
- **Halogen Free**
- SON 5mm x 6mm Plastic Package

APPLICATIONS

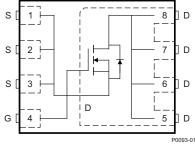
- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and **Computing Systems**
- **Optimized for Control FET Applications**

DESCRIPTION

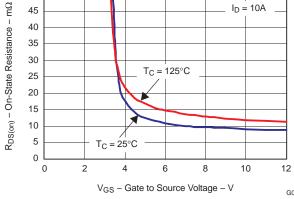
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The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.





$R_{DS(ON)}$ vs V_{GS}



PRODUCT SUMMARY

V _{DS}	Drain to Source Voltage	25	V	
Q_g	Gate Charge Total (4.5V) 2.9			nC
Q_{gd}	Gate Charge Gate to Drain	0.7		nC
D	Drain to Source On Resistance	$V_{GS} = 4.5V$	13	mΩ
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 10V	9	mΩ
V _{GS(th)}	Threshold Voltage	2		V

ORDERING INFORMATION

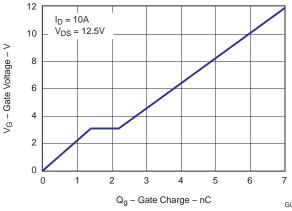
Device	Package	Media	Qty	Ship	
CSD16412Q5A	SON 5 × 6 Plastic Package	13-inch reel	2500	Tape and Reel	

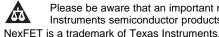
ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	٧
V_{GS}	Gate to Source Voltage	+16 / –12	V
	Continuous Drain Current, T _C = 25°C	52	Α
I _D	Continuous Drain Current ⁽¹⁾	14	Α
I_{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	91	Α
P _D	Power Dissipation ⁽¹⁾	3	W
T_J , T_{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse $I_D=17A,L=0.1mH,R_G=25\Omega$	14	mJ

- (1) $R_{\theta JA} = 42^{\circ}C/W$ on $1in^2$ Cu (2 oz) on 0.060" thick FR4 PCB.
- (2) Pulse width ≤300µs, duty cycle ≤2%

Gate Charge





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ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	haracteristics	·				
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$	25			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 20V			1	μA
I _{GSS}	Gate to Source Leakage Current	V _{DS} = 0V, V _{GS} = +16/-12V			100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.7	2.0	2.3	V
<u> </u>	Dunin to Course On Bonintones	V _{GS} = 4.5V, I _D = 10A		13	16	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 10V, I_D = 10A$		9	11	mΩ
9 _{fs}	Transconductance	V _{DS} = 15V, I _D = 10A		33		S
Dynamic	Characteristics					
C _{ISS}	Input Capacitance			410	530	pF
Coss	Output Capacitance	V _{GS} = 0V, V _{DS} = 12.5V, f = 1MHz		350	450	pF
C _{RSS}	Reverse Transfer Capacitance			32	42	pF
R _g	Series Gate Resistance			0.7	1.4	Ω
Qg	Gate Charge Total (4.5V)			2.9	3.8	nC
Q _{gd}	Gate Charge Gate to Drain	V 40.5V I 40A		0.7		nC
Q _{gs}	Gate Charge Gate to Source	$V_{DS} = 12.5V, I_{D} = 10A$		1.4		nC
Qg(th)	Gate Charge at Vth			0.9		nC
Q _{OSS}	Output Charge	$V_{DS} = 13V$, $V_{GS} = 0V$		7		nC
t _{d(on)}	Turn On Delay Time			5.5		ns
t _r	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V, I_{D} = 10A$		7.1		ns
t _{d(off)}	Turn Off Delay Time	$R_G = 2\Omega$		5.7		ns
t _f	Fall Time			3.3		ns
Diode Cl	haracteristics	·	•			
V_{SD}	Diode Forward Voltage	I _S = 10A, V _{GS} = 0V		0.85	1.0	V
Q _{rr}	Reverse Recovery Charge	$V_{dd} = 13V$, $I_F = 10A$, $di/dt = 300A/\mu s$		12		nC
t _{rr}	Reverse Recovery Time	V_{dd} = 13V, I_F = 10A, di/dt = 300A/ μ s		16		ns

THERMAL CHARACTERISTICS

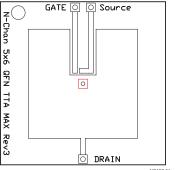
 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	MIN	TYP	MAX	UNIT
R _{θJC}	Thermal Resistance Junction to Case ⁽¹⁾			3.7	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient ⁽¹⁾ (2)			53	°C/W

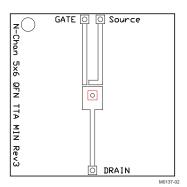
R $_{\theta JC}$ is determined with the device mounted on a 1 inch square 2 oz. Cu pad on a 1.5 × 1.5 in 0.060 inch thick FR4 board. R $_{\theta JC}$ is specified by design while R $_{\theta JA}$ is determined by the user's board design. Device mounted on FR4 Material with 1 inch² of 2 oz. Cu.

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Max $R_{\theta JA} = 53^{\circ}C/W$ when mounted on 1inch² of 2 oz. Cu.



Max $R_{\theta JA} = 119^{\circ} C/W$ when mounted on minimum pad area of 2 oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

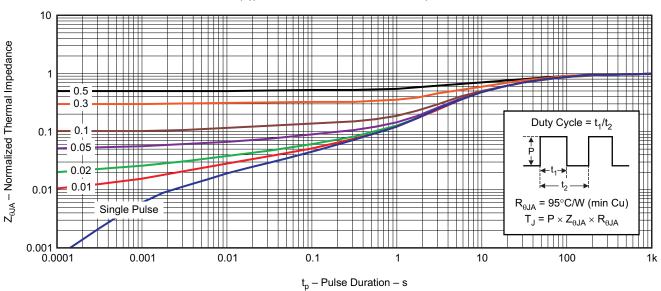


Figure 1. Transient Thermal Impedance

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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

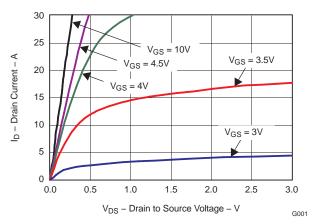


Figure 2. Saturation Characteristics

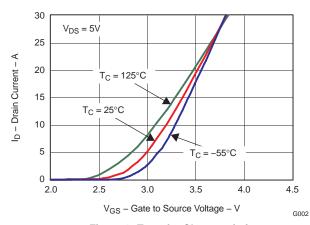


Figure 3. Transfer Characteristics

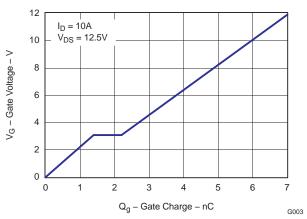


Figure 4. Gate Charge

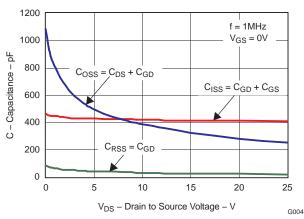


Figure 5. Capacitance

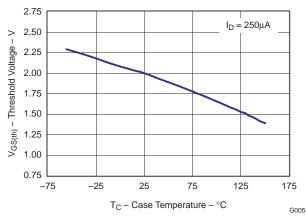


Figure 6. Threshold Voltage vs. Temperature

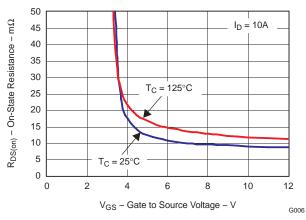


Figure 7. On Resistance vs. Gate Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

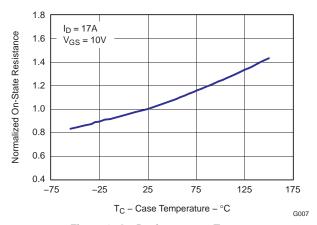


Figure 8. On Resistance vs. Temperature

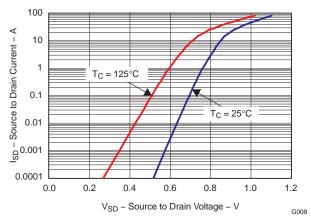


Figure 9. Typical Diode Forward Voltage

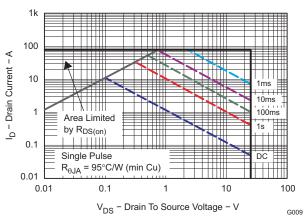


Figure 10. Maximum Safe Operating Area

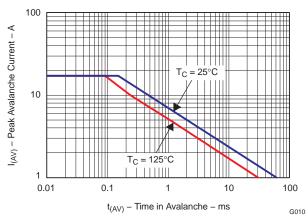


Figure 11. Single Pulse Unclamped Inductive Switching

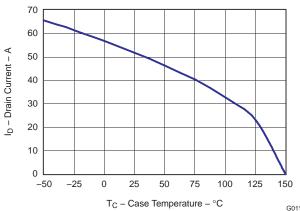
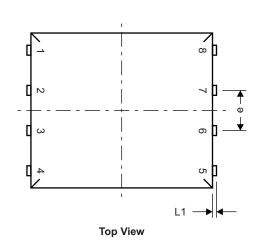


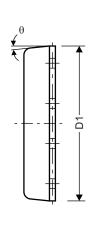
Figure 12. Maximum Drain Current vs. Temperature



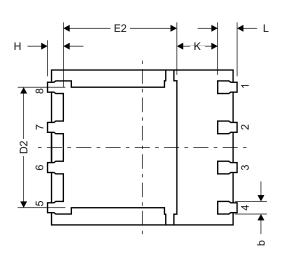
MECHANICAL DATA

Q5A Package Dimensions





Side View



θ E1 E Front View

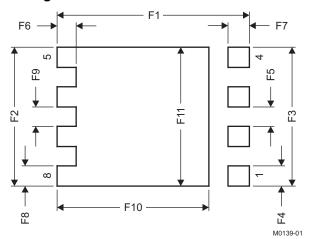
Bottom View

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DIM	MILLIMETERS						
	MIN	NOM	MAX				
А	0.90	1.00	1.10				
b	0.33	0.41	0.51				
С	0.20	0.25	0.30				
D1	4.80	4.90	5.00				
D2	3.61	3.81	3.96				
Е	5.90	6.00	6.10				
E1	5.70	5.75	5.80				
E2	3.38	3.58	3.78				
е		1.27 BSC					
Н	0.41	0.51	0.61				
K	1.10						
L	0.51	0.61	0.71				
L1	0.06	0.13	0.20				
θ	0°		12°				



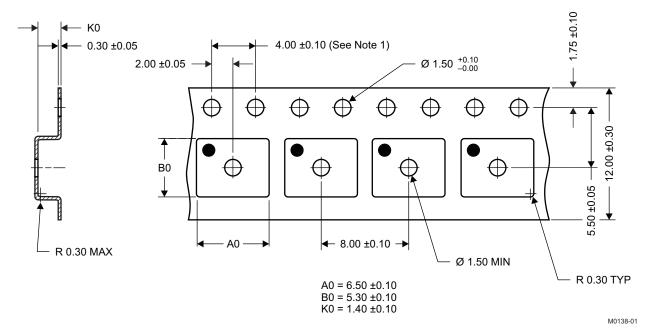
Figure 13. Recommended PCB Pattern



DIM	MILLIM	IETERS	INCHES		
DIN	MIN	MAX	MIN	MAX	
F1	6.205	6.305	0.244	0.248	
F2	4.46	4.56	0.176	0.18	
F3	4.46	4.56	0.176	0.18	
F4	0.65	0.7	0.026	0.028	
F5	0.62	0.67	0.024	0.026	
F6	0.63	0.68	0.025	0.027	
F7	0.7	0.8	0.028	0.031	
F8	0.65	0.7	0.026	0.028	
F9	0.62	0.67	0.024	0.026	
F10	4.9	5	0.193	0.197	
F11	4.46	4.56	0.176	0.18	

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5A Tape and Reel Information



Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible

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REVISION HISTORY

Cł	hanges from Original (August 2009) to Revision A	Page	(
•	Deleted the Package Marking Information section		

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16412Q5A	SON	DQJ	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

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*All dimensions are nominal

ĺ	Device	Package Type	ackage Type Package Drawing		SPQ	Length (mm)	Width (mm)	Height (mm)	
	CSD16412Q5A	SON	DQJ	8	2500	340.0	340.0	38.0	

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